

NCE50TD120VT

1200V, 50A, Trench FS II Fast IGBT

General Description:

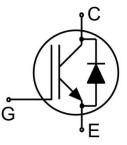
Using NCE's proprietary trench design and advanced FS (Field Stop) second generation technology, the 1200V Trench FSII IGBT offers superior conduction and switching performances, and easy parallel operation;

Features

- Trench FSII Technology Offering
- Very low V_{CE(sat)}
- High speed switching
- Positive temperature coefficient in V_{CE(sat)}
- Very tight parameter distribution
- High ruggedness, temperature stable behavior

Application

- PV power
- Three-level Solar String Inverter



Schematic diagram

Package Marking and Ordering Information

Device	Device Package	Device Marking
NCE50TD120VT	TO-247	NCE50TD120VT



TO-247

Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CES}	Collector-Emitter Voltage	1200	V
V _{GES}	Gate- Emitter Voltage	±30	V
1.	Collector Current	100	Α
Ic	Collector Current @Tc = 100 °C	50	Α
I _{Cplus}	Pulsed Collector Current, t_p limited by T_{jmax}	150	Α
-	turn off safe operating area, V_{CE} =1200V, Tj =150°C	150	Α
I _F	Diode Continuous Forward Current @T _C = 100 °C	50	Α
I _{FM}	Diode Maximum Forward Current	150	Α
В	Power Dissipation @ T _C = 25°C	535	W
P _D	Power Dissipation @T _C = 100 °C	268	W
T_{J} , T_{stg}	Operating Junction and Storage Temperature Range	-55 to +175	°C
T _L	Maximum Temperature for Soldering	260	°C



Thermal Characteristic

Symbol	Parameter	Value	Units
R ₀ JC	Thermal Resistance, Junction to case for IGBT	0.28	°C/W
R ₀ JC	Thermal Resistance, Junction to case for Diode	0.50	°C/W
R _{θJA}	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (T_C=25°C unless otherwise noted)

Cumb al		Tool Co	-		Value		
Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
Static Chara	cteristics						
V _{(BR)CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V	,I _{CE} =1mA	1200			V
I _{CES}	Collector-Emitter Leakage Current	V _{GE} =0V,	/ _{CE} =1200V			5	uA
I _{GES(F)}	Gate to Emitter Forward Leakage	V _{GE} =+30	V,V _{CE} =0V			200	nA
I _{GES(R)}	Gate to Source Reverse Leakage	V _{GE} =-30	V,V _{CE} =0V			200	nA
V	Callegates Fraittes Catamatics Voltage	Ic=50A	Tj=25°C		1.85	2.05	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	V _{GE} =15V	Tj=150°C		2.05		V
$V_{\text{GE(th)}}$	Gate Threshold Voltage	I _C =1mA	,V _{CE} =V _{GE}	4.5		6.5	V
Dynamic Ch	aracteristics	•			•		
C _{ies}	Input Capacitance				6980		pF
Coes	Output Capacitance		V _{CE} =30V,V _{GE} =0V,		220		
Cres	Reverse Transfer Capacitance	f=1MHz			167		
Qg	Total Gate Charge				370		nC
Q _{ge}	Gate to Emitter Charge	V_{CC} =960V, I_{C} =50A, V_{GE} =15V			65		
Q _{gc}	Gate to Collector Charge		101		211		
Switching C	haracteristics						
t _{d(ON)}	Turn-on Delay Time				19		
t _r	Rise Time				17		
t _{d(OFF)}	Turn-Off Delay Time	V _{CE} =600	V _{CE} =600V,I _C =50A,		170		ns
t _f	Fall Time	V_{GE} =0/15V, R_g =8 Ω			18		
Eon	Turn-On Switching Loss	Inducti	ve Load		2.6		
E _{off}	Turn-Off Switching Loss				1.7		mJ
E _{ts}	Total Switching Loss				4.3		

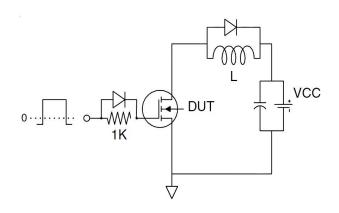
Electrical Characteristics of the Diode(T_C = 25°C unless otherwise specified):

Symbol	Parameter	Test Conditions	Rating			Unito
			Min.	Тур.	Max.	Units
V _{FM}	Diode Forward Voltage	I _F =50A		2.2	3.0	V
Trr	Reverse Recovery Time	L -05A		150		ns
I _{RRM}	Diode Peak Reverse Recovery Current	Recovery Current I _F =25A, di/dt=700A/us		10		Α
Qrr	Reverse Recovery Charge	ui/ui-700A/us		2.2		uC
Pulse width t _{tp} ≤380μs,δ≤2%						

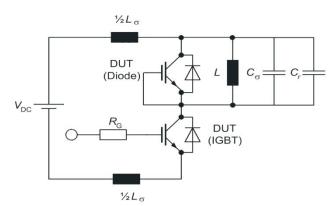


Test Circuit

1) Gate Charge Test Circuit

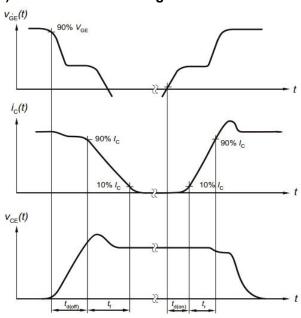


2) Switch Time Test Circuit

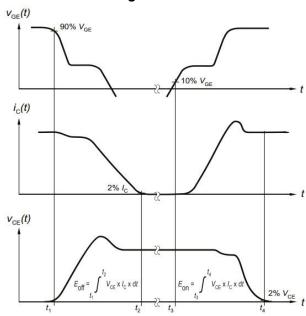


Switching characteristics

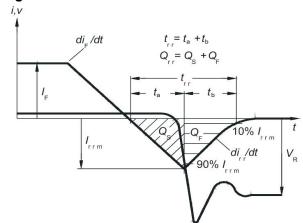
1) Definition of switching times



2) Definition of switching losses



3) Definition of diode switching characteristics





Typical Electrical and Thermal Characteristics

Figure 1 Output Characteristics

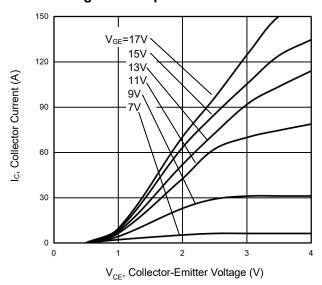


Figure 3 V_{CE(sat)} vs. Case Temperature

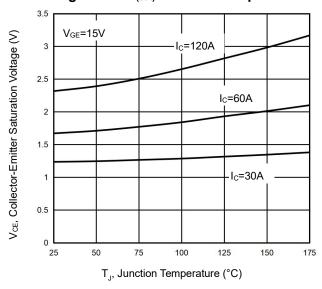


Figure 5 Capacitance Characteristics

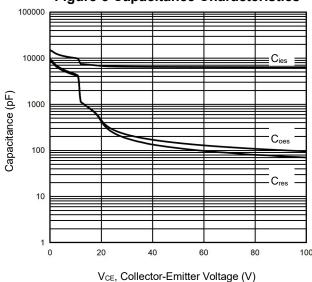


Figure 2 Transfer Characteristics

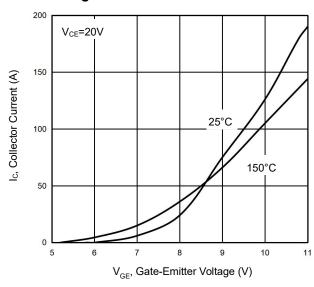


Figure 4 Saturation Voltage vs. V_{GE}

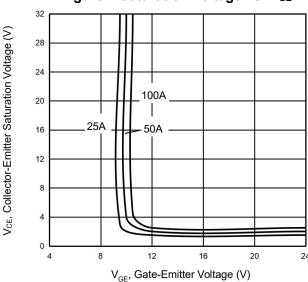
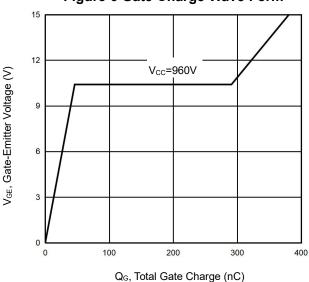


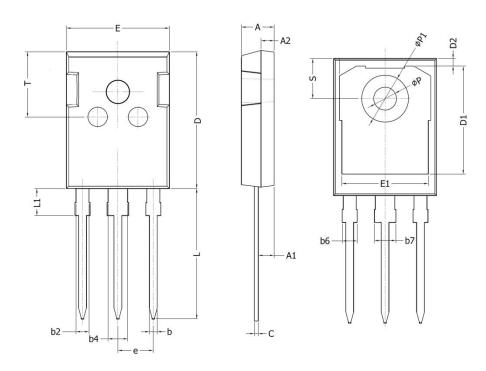
Figure 6 Gate Charge Wave Form



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TO-247 Package Information



Comple ed	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.90	5.10	0.193	0.201	
A1	2.31	2.51	0.091	0.099	
A2	1.9	2.1	0.075	0.083	
b	1.16	1.26	0.046	0.050	
b2	1.96	2.06	0.077	0.081	
b4	2.96	3.06	0.117	0.120	
b6	-	2.25	-	0.089	
b7	-	3.25	-	0.128	
С	0.59	0.66	0.023	0.026	
D	20.90	21.10	0.823	0.831	
D1	16.25	16.85	0.640	0.663	
D2	1.05	1.35	0.041	0.053	
E	15.70	15.90	0.618	0.626	
E1	13.10	13.50	0.516	0.531	
е	5.436	BSC	0.214 BSC		
L	19.80	20.10	0.780	0.791	
L1	-	4.30	-	0.169	
Р	3.40	3.60	0.134	0.142	
P1	7.00	7.40	0.276	0.291	
S	6.05	6.25	0.238	0.246	
Т	9.80	10.20	0.386	0.402	





NCE50TD120VT

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